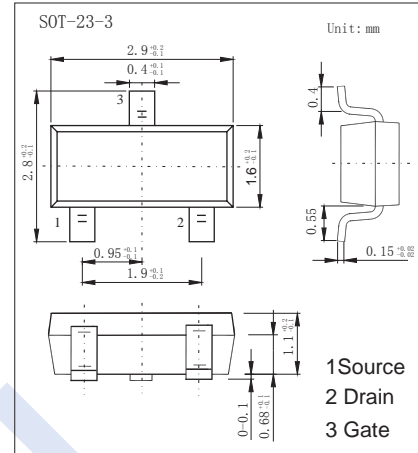


## N-Channel Junction Silicon FET

### 2SK303

#### ■ Features

- Ideal for potentiometers, analog switches, low frequency amplifiers, constant current supplies, and impedance conversion.



#### ■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Drain to source voltage	V <sub>DSS</sub>	30	V
Gate to Drain voltage	V <sub>GDS</sub>	-30	V
Gate current	I <sub>G</sub>	10	m A
Drain current	I <sub>D</sub>	20	m A
Power dissipation	P <sub>D</sub>	200	mW
Channel temperature	T <sub>ch</sub>	150	°C
Storage temperature	T <sub>stg</sub>	-55 to +150	°C

\* PW ≤ 10 us, Duty Cycle ≤ 1%

#### ■ Electrical Characteristics Ta = 25°C

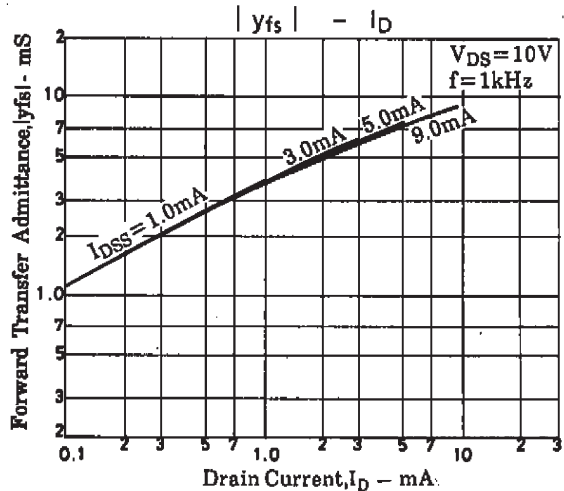
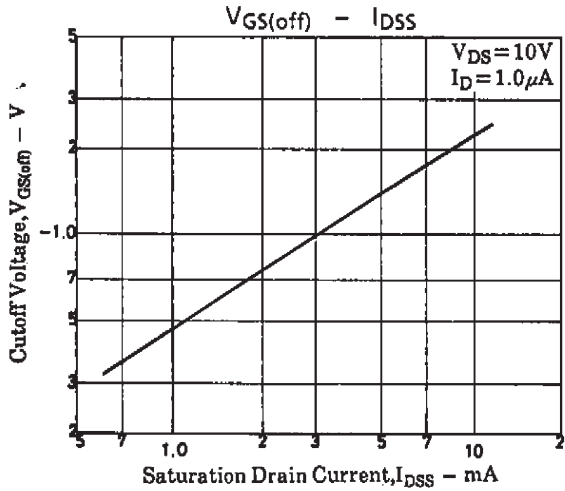
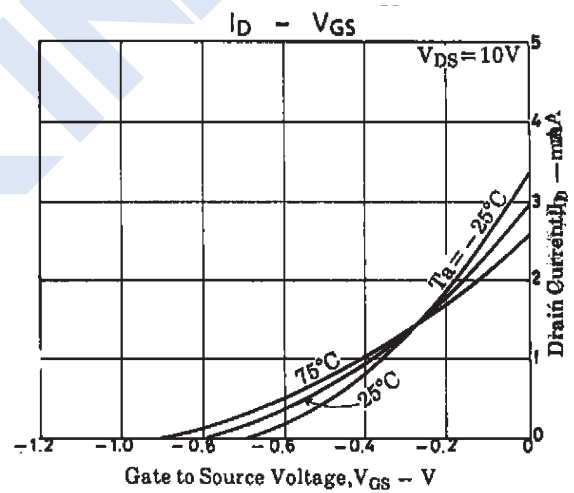
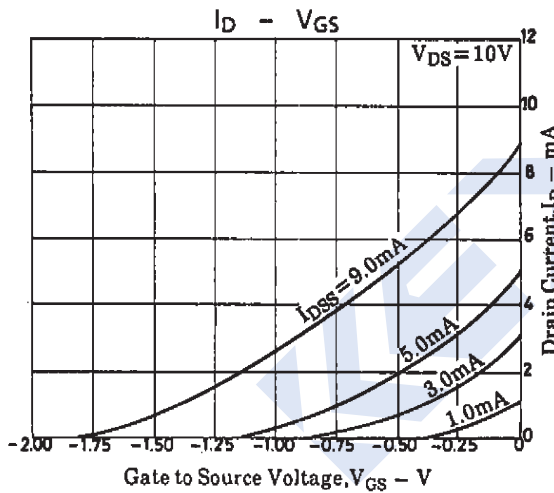
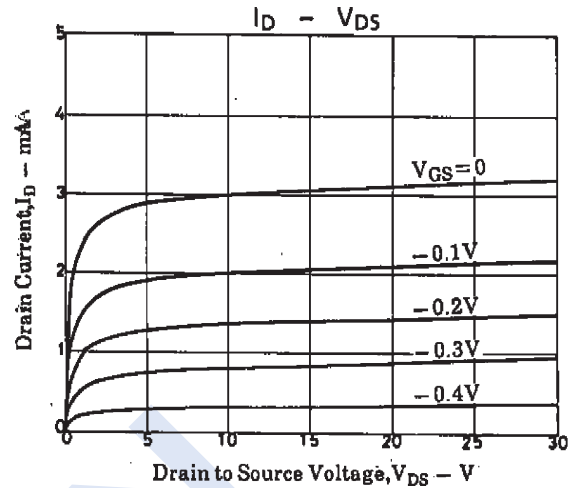
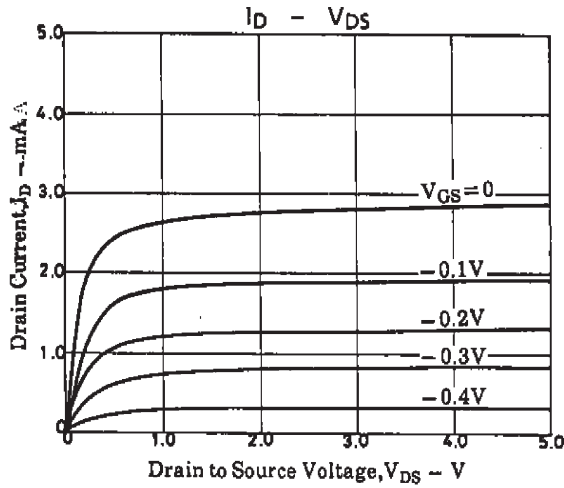
Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Gate to drain	V <sub>GDS</sub>	I <sub>G</sub> = -10 μ A	-30			V
Gate to source leakage current	I <sub>GSS</sub>	V <sub>GS</sub> = -20V			-1.0	nA
Drain cut-off current	I <sub>DSS</sub>	V <sub>DS</sub> = 10V, V <sub>GS</sub> = 0	0.6		12.0	mA
Cutoff voltage	V <sub>GS(off)</sub>	V <sub>DS</sub> = 10V, I <sub>D</sub> = 1 μ A		-1	-4	V
Forward transfer admittance	Y <sub>fs</sub>	V <sub>DS</sub> = 10V, V <sub>GS</sub> = 0, f = 1KHz	2.5	6.0		ms
Drain to source on-state resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> = 0, V <sub>DS</sub> = 10mV		250		Ω
Input capacitance	C <sub>iss</sub>	V <sub>DS</sub> = 10V, V <sub>GS</sub> = 0, f = 1MHZ		5		pF
Reverse transfer capacitance	C <sub>rss</sub>			1.5		pF

#### ■ I<sub>DSS</sub> Classification unit:mA

Marking	V2	V3	V4	V5
Rank	2	3	4	5
I <sub>DSS</sub>	0.6~1.5	1.2~3	2.5~6	5~12

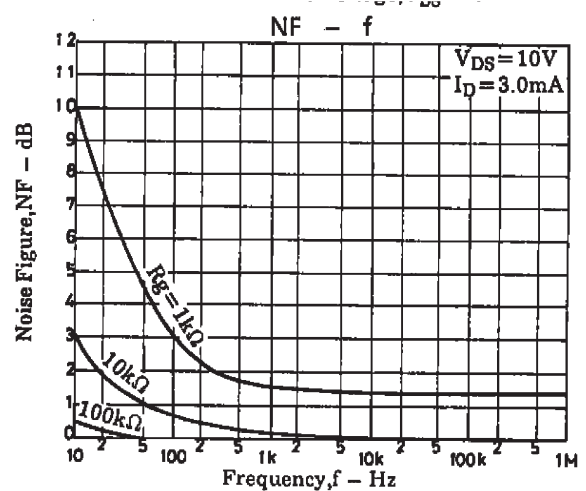
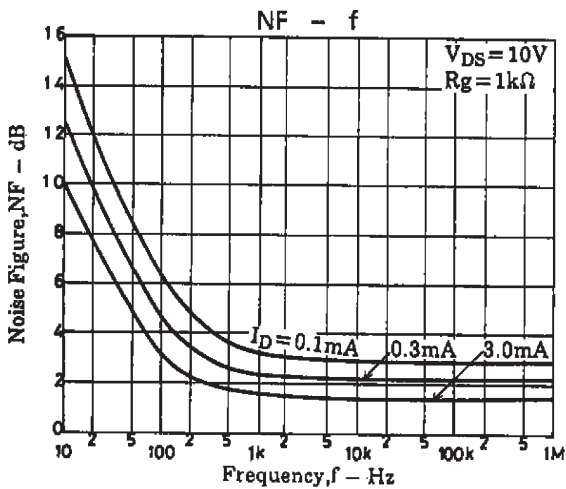
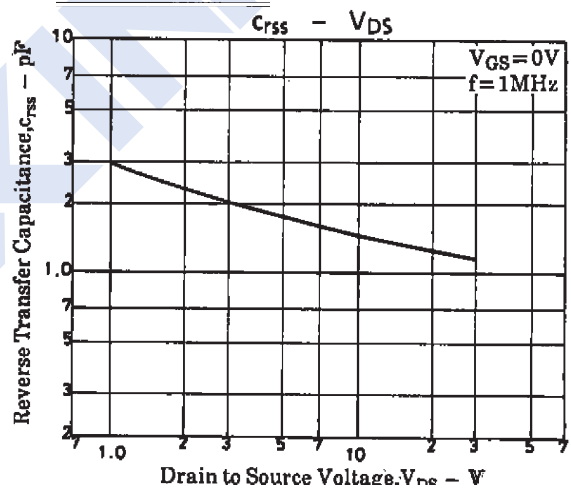
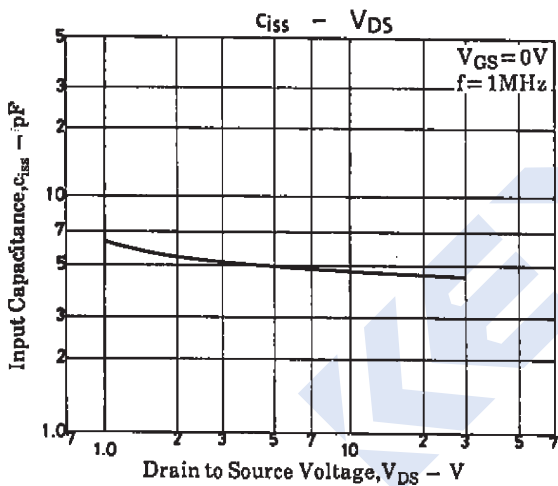
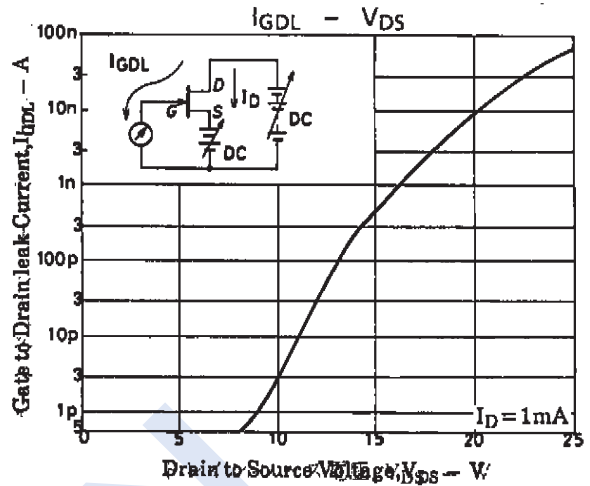
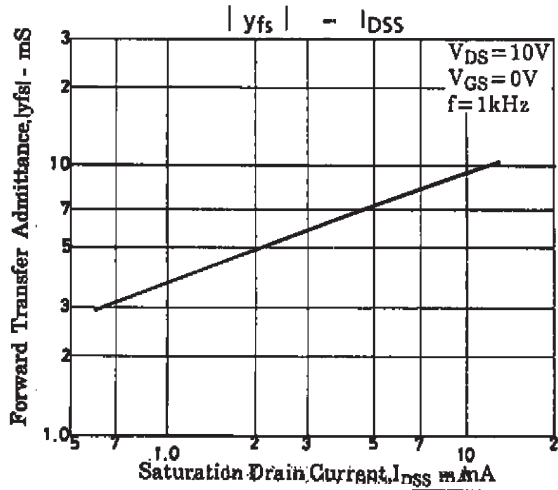
## N-Channel Junction Silicon FET 2SK303

■ Typical Characteristics



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■ Typical Characteristics



## N-Channel Junction Silicon FET 2SK303

### ■ Typical Characteristics

